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SEMICONDUCTOR TM

June 2000 PRELIMINARY

FDC604P

FDC604P

P-Channel 1.8V Specified PowerTrench[®] MOSFET

General Description

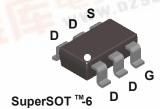
This P-Channel 1.8V specified MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for battery power management applications.

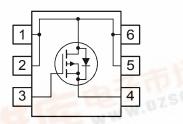
Applications

- Battery management
- Load switch
- Battery protection

Features

- -5.5 A, -20 V. $R_{DS(ON)} = 0.033 \ \Omega \ @V_{GS} = -4.5 \ V$ $R_{DS(ON)} = 0.043 \ \Omega \ @V_{GS} = -2.5 \ V$ $R_{DS(ON)} = 0.060 \ \Omega \ @V_{GS} = -1.8 \ V$
- Fast switching speed.
- High performance trench technology for extremely
 low R_{DS(ON)}





Absolute Maximum Ratings T_{A=25[°]C unless otherwise noted}

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-Source Voltage		-20	V	
V _{GSS}	Gate-Source Voltage		±8	V	
ID	Drain Current – Continuous	(Note 1a)	-5.5	А	
	– Pulsed		-20	- 55	
PD	Maximum Power Dissipation	(Note 1a)	1.6	W	
		(Note 1b)	0.8	0.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C	
Therma	I Characteristics	190	21217		
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.604	FDC604P	7"	8mm	3000 units



FDC604P Rev B (W)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = -250 \mu A$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250 µA,Referenced to 25°C		-12		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 V$, $V_{GS} = 0 V$			-1	μA
I _{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 8 V$, $V_{DS} = 0 V$			100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = -8 V V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-0.4	-0.7	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$ \begin{array}{ccc} V_{GS} = -4.5 \ V, & I_D = -5.5 \ A \\ V_{GS} = -2.5 \ V, & I_D = -4.8 \ A \\ V_{GS} = -1.8 \ V, & I_D = -4.0 \ A \end{array} $		0.024 0.030 0.042	0.033 0.043 0.060	Ω
I _{D(on)}	On–State Drain Current	$V_{GS} = -4.5 V$, $V_{DS} = -5 V$	-20			Α
g fs	Forward Transconductance	$V_{DS} = -5 V$, $I_D = -3.5 A$		23		S
Dynamic	c Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 V$, $V_{GS} = 0 V$,		1926		pF
Coss	Output Capacitance	f = 1.0 MHz		530		pF
C _{rss}	Reverse Transfer Capacitance			185		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn–On Delay Time	$V_{DD} = -10 V$, $I_D = -1 A$,		13	23	ns
t _r	Turn–On Rise Time	V_{GS} = -4.5 V, R_{GEN} = 6 Ω		11	20	ns
t _{d(off)}	Turn–Off Delay Time			90	144	ns
t _f	Turn–Off Fall Time			45	72	ns
Qg	Total Gate Charge	$V_{DS} = -10 V$, $I_D = -3.5 A$,		19	30	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 V$		4		nC
Q _{gd}	Gate–Drain Charge			7.5		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
ls	Maximum Continuous Drain-Source	Diode Forward Current			-1.3	А
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$, $I_S = -1.3 A$ (Note 2)		-0.7	-1.2	V

Notes:

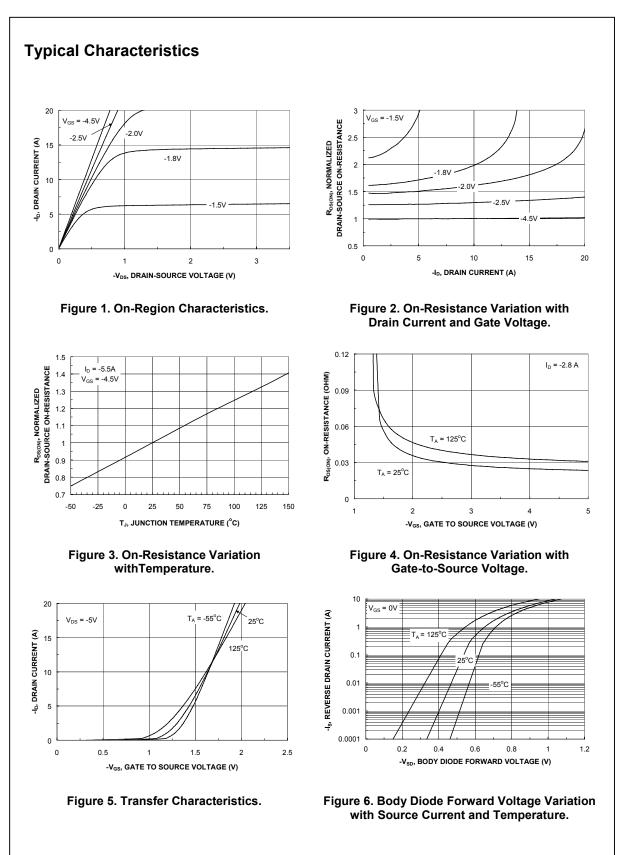
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a. 78°C/W when mounted on a $1in^2$ pad of 2oz copper on FR-4 board.

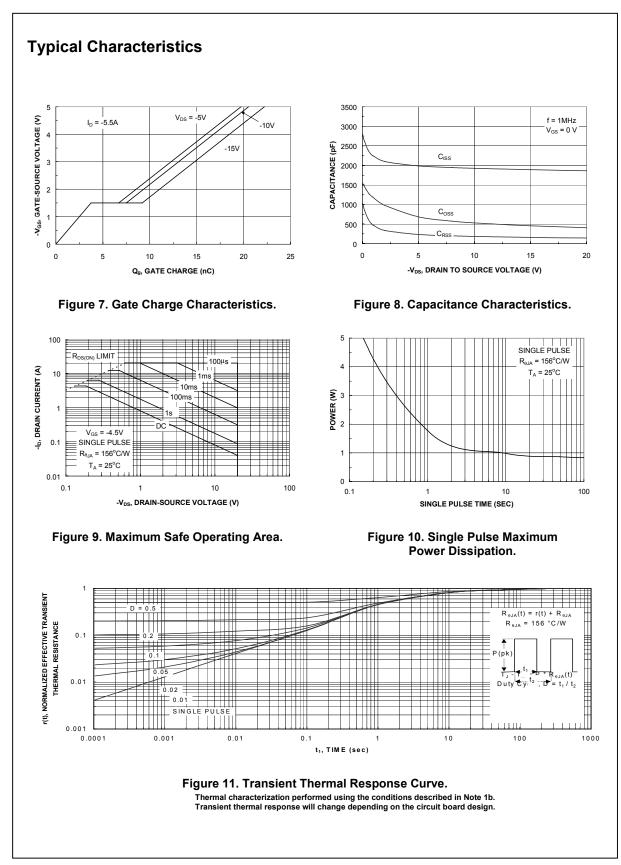
b. 156°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width $\leq 300~\mu s,~\text{Duty}~\text{Cycle} \leq 2.0\%$

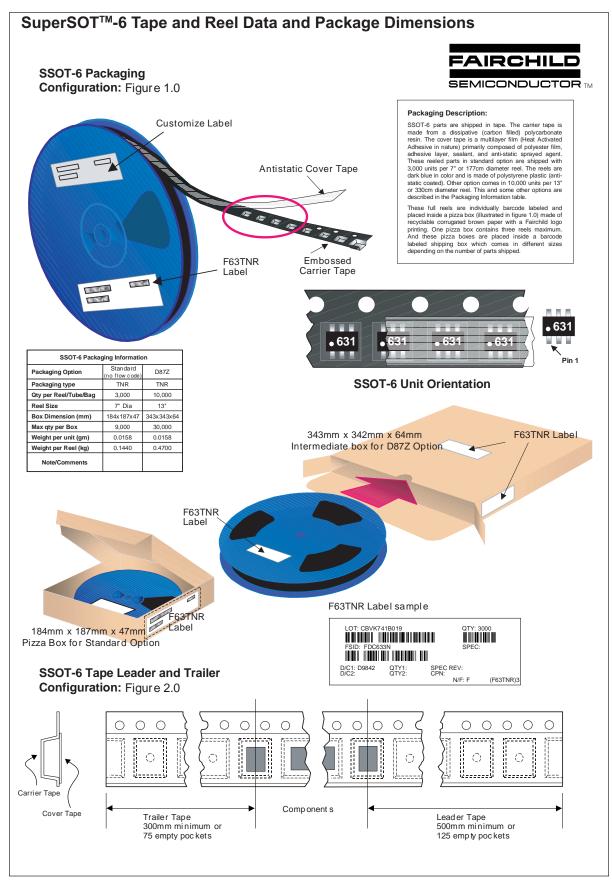
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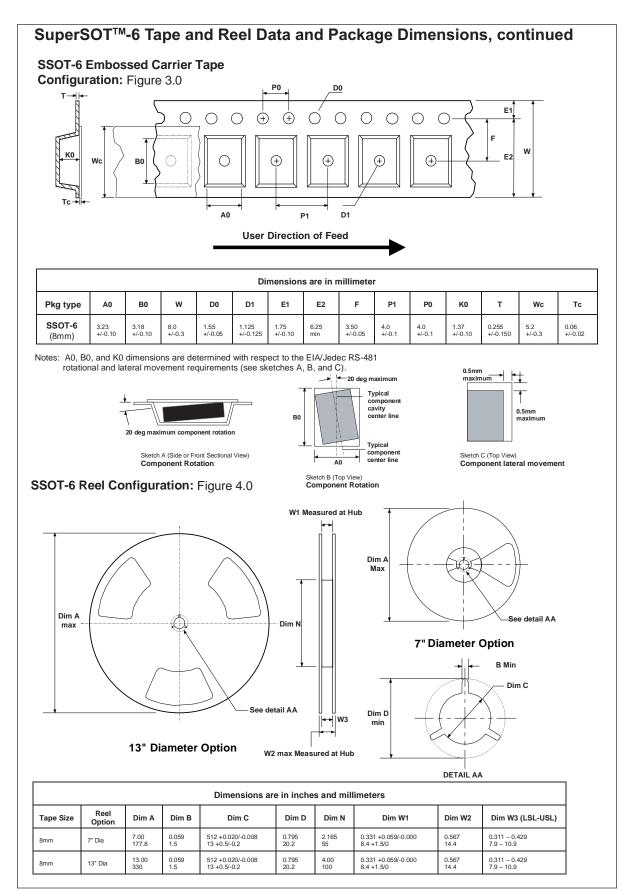


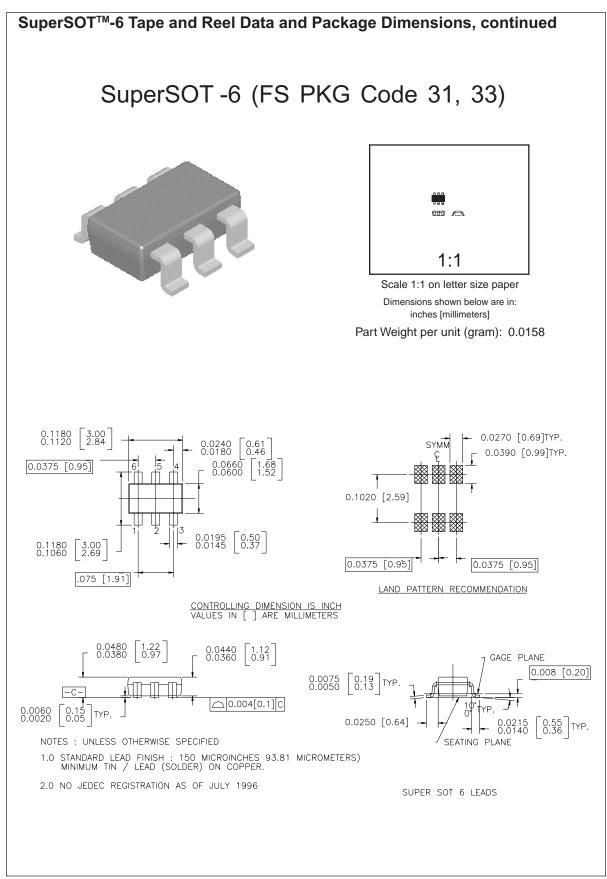
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SuperSOT[™]-8 SyncFET[™] TinyLogic[™] UHC[™] VCX[™]

PRODUCT STATUS DEFINITIONS

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Datasheet Identification	Product Status	Definition This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.		
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